Power LDMOS transistor

**AMPLEON** 

Rev. 3 — 1 September 2015

Product data sheet

### 1. Product profile

### 1.1 General description

A 600 W LDMOS RF power transistor for transmitter applications and industrial applications. The excellent ruggedness of this device makes it ideal for digital and analog transmitter applications.

Table 1. Application information

Test signal	f (MHz)	P <sub>L(AV)</sub> (W)	P <sub>L(M)</sub> (W)	G <sub>p</sub> (dB)	η <sub>D</sub> (%)	IMD3 (dBc)
RF performance in a co	ommon source 860 MHz na	arrowband	l test circ	uit		
2-tone, class-AB	f <sub>1</sub> = 860; f <sub>2</sub> = 860.1	250	-	20.8	46	-32
pulsed, class-AB	860	-	600	19.8	58	-

### 1.2 Features and benefits

- Excellent ruggedness (VSWR ≥ 40 : 1 through all phases)
- Optimum thermal behavior and reliability, R<sub>th(i-c)</sub> = 0.15 K/W
- High power gain
- High efficiency
- Designed for broadband operation (400 MHz to 1000 MHz)
- Internal input matching for high gain and optimum broadband operation
- Excellent reliability
- Easy power control
- Compliant to Directive 2002/95/EC, regarding Restriction of Hazardous Substances (RoHS)

### 1.3 Applications

- Communication transmitter applications
- Industrial applications

## 2. Pinning information

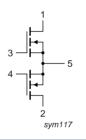
Table 2. Pinning

Pin	Description		Simplified outline	Graphic symbol
BLF10H660	00P (SOT539A)			
1	drain1			,
2	drain2		1 2	1 
3	gate1		5	3
4	gate2		3 4	5
5	source	<u>[1]</u>		4
				2 sym117

### **BLF10H6600PS (SOT539B)**

1	drain1	
2	drain2	
3	gate1	
4	gate2	
5	source	[1]





[1] Connected to flange.

## 3. Ordering information

Table 3. Ordering information

Type number	Package							
	Name	Description	Version					
BLF10H6600P	-	flanged balanced ceramic package; 2 mounting holes; 4 leads	SOT539A					
BLF10H6600PS	-	earless flanged balanced ceramic package; 4 leads	SOT539B					

## 4. Limiting values

Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage		-	110	V
$V_{GS}$	gate-source voltage		-0.5	+11	V
T <sub>stg</sub>	storage temperature		-65	+150	°C
Tj	junction temperature	1	1 -	225	°C

<sup>[1]</sup> Continuous use at maximum temperature will affect the reliability. For details refer to the on-line MTF calculator.

BLF10H6600P\_BLF10H6600PS#3

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### 5. Thermal characteristics

#### Table 5. Thermal characteristics

Symbol	Parameter	Conditions		Тур	Unit
$R_{th(j-c)}$	thermal resistance from junction to case	$T_{case}$ = 80 °C; $P_{L(AV)}$ = 250 W	[1]	0.15	K/W

<sup>[1]</sup>  $R_{th(j-c)}$  is measured under RF conditions.

## 6. Characteristics

Table 6. DC characteristics

 $T_i = 25$  °C; per section unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{(BR)DSS}$	drain-source breakdown voltage	$V_{GS}$ = 0 V; $I_D$ = 2.4 mA	[1]	110	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$V_{DS}$ = 10 V; $I_{D}$ = 240 mA	[1]	1.4	1.9	2.4	V
I <sub>DSS</sub>	drain leakage current	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}$		-	-	2.8	μА
I <sub>DSX</sub>	drain cut-off current	$V_{GS} = V_{GS(th)} + 3.75 V;$ $V_{DS} = 10 V$		-	36	-	Α
I <sub>GSS</sub>	gate leakage current	$V_{GS}$ = 10 V; $V_{DS}$ = 0 V		-	-	280	nA
R <sub>DS(on)</sub>	drain-source on-state resistance	$V_{GS} = V_{GS(th)} + 3.75 \text{ V};$ $I_D = 8.5 \text{ A}$	<u>[1]</u>	-	143	-	mΩ

<sup>[1]</sup>  $I_D$  is the drain current.

Table 7. AC characteristics

 $T_i = 25$  °C; per section unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
C <sub>iss</sub>	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	220	-	pF
Coss	output capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 50 \text{ V}; f = 1 \text{ MHz}$	-	74	-	pF
C <sub>rss</sub>	reverse transfer capacitance	V <sub>GS</sub> = 0 V; V <sub>DS</sub> = 50 V; f = 1 MHz	-	1.2	-	pF

<sup>[1]</sup> Capacitance values without internal matching.

### Table 8. RF characteristics

RF characteristics in Ampleon production narrowband test circuit;  $T_{\text{case}} = 25 \, ^{\circ}\text{C}$  unless otherwise specified.

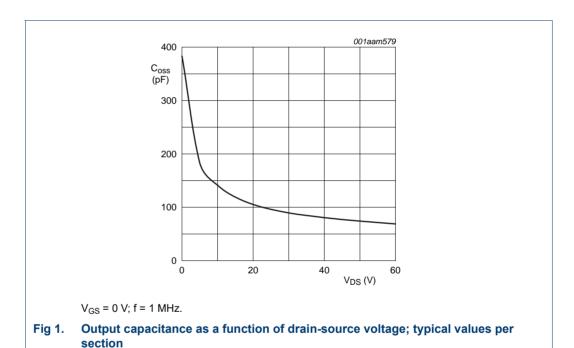
Symbol	Parameter	Conditions		Min	Тур	Max	Unit
2-Tone, o	class-AB						
$V_{DS}$	drain-source voltage			-	50	-	V
I <sub>Dq</sub>	quiescent drain current		[1]	-	1.3	-	Α
P <sub>L(AV)</sub>	average output power	f <sub>1</sub> = 860 MHz; f <sub>2</sub> = 860.1 MHz		250	-	-	W
Gp	power gain	f <sub>1</sub> = 860 MHz; f <sub>2</sub> = 860.1 MHz		19.8	20.8	-	dB
$\eta_{D}$	drain efficiency	f <sub>1</sub> = 860 MHz; f <sub>2</sub> = 860.1 MHz		42	46	-	%
IMD3	third-order intermodulation distortion	f <sub>1</sub> = 860 MHz; f <sub>2</sub> = 860.1 MHz		-	-32	-28	dBc

Table 8. RF characteristics ... continued

RF characteristics in Ampleon production narrowband test circuit;  $T_{case} = 25$  °C unless otherwise specified.

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
Pulsed,	class-AB						
$V_{DS}$	drain-source voltage			-	50	-	V
I <sub>Dq</sub>	quiescent drain current		[1]	-	1.3	-	Α
P <sub>L(M)</sub>	peak output power	f = 860 MHz		-	600	-	W
Gp	power gain	f = 860 MHz		17.2	19.8	-	dB
$\eta_{D}$	drain efficiency	f = 860 MHz		54	58	-	%
t <sub>p</sub>	pulse duration			-	100	-	μS
δ	duty cycle			-	20	-	%

[1] I<sub>Dq</sub> for total device



### 7. Test information

### 7.1 Ruggedness in class-AB operation

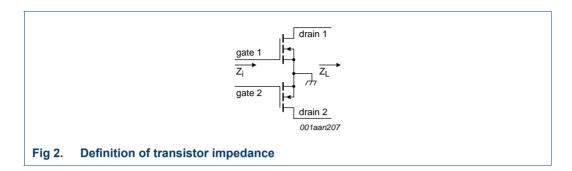
The BLF10H6600P and BLF10H6600PS are capable of withstanding a load mismatch corresponding to VSWR  $\geq$  40 : 1 through all phases under the following conditions: V<sub>DS</sub> = 50 V; I<sub>Dq</sub> = 1.3 A; P<sub>L</sub> = 600 W (pulsed); f = 860 MHz.

## 7.2 Impedance information

Table 9. Typical push-pull impedance

Simulated  $Z_i$  and  $Z_L$  device impedance; impedance info at  $V_{DS} = 50 \text{ V}$  and  $P_{L(AV)} = 600 \text{ W}$  (pulsed CW). See <u>Figure 2</u> for definition of transistor impedance.

f	Z <sub>i</sub>	Z <sub>L</sub>
MHz	Ω	Ω
300	0.607 + j0	5.495 + j1.936
325	0.622 – j1.441	5.324 + j2.008
350	0.639 – j1.121	5.151 + j2.065
375	0.658 – j0.826	4.977 + j2.107
400	0.679 – j0.551	4.805 + j2.136
425	0.703 – j0.291	4.634 + j2.153
450	0.73 - j0.044	4.466 + j2.157
475	0.76 + j0.194	4.301 + j2.151
500	0.793 + j0.424	4.14 + j2.134
525	0.83 + j0.648	3.984 + j2.109
550	0.872 + j0.869	3.833 + j2.075
575	0.919 + j1.088	3.687 + j2.033
600	0.972 + j1.305	3.546 + j1.985
625	1.032 + j1.523	3.411 + j1.931
650	1.101 + j1.741	3.281 + j1.871
675	1.179 + j1.963	3.156 + j1.807
700	1.268 + j2.187	3.036 + j1.738
725	1.371 + j2.416	2.922 + j1.666
750	1.49 + j2.651	2.813 + j1.591
775	1.629 + j2.891	2.708 + j1.512
800	1.792 + j3.138	2.609 + j1.432
825	1.984 + j3.39	2.514 + j1.349
850	2.212 + j3.649	2.423 + j1.264
875	2.484 + j3.91	2.336 + j1.178
900	2.812 + j4.17	2.254 + j1.091
925	3.209 + j4.421	2.175 + j1.003
950	3.689 + j4.648	2.1 + j0.913
975	4.27 + j4.829	2.029 + j0.823
1000	4.967 + j4.927	1.96 + j0.733



### 7.3 Test circuit information

### Table 10. List of components

For test circuit, see Figure 3, Figure 4 and Figure 5.

Component	Description	Value		Remarks
B1, B2	semi rigid coax	25 $Ω$ ; 49.5 mm		UT-090C-25 (EZ 90-25)
C1	multilayer ceramic chip capacitor	12 pF	<u>[1]</u>	
C2, C3, C4, C5, C6	multilayer ceramic chip capacitor	8.2 pF	<u>[1]</u>	
C7	multilayer ceramic chip capacitor	6.8 pF	[2]	
C8	multilayer ceramic chip capacitor	2.7 pF	[2]	
C9	multilayer ceramic chip capacitor	2.2 pF	[2]	
C10, C13, C14	multilayer ceramic chip capacitor	100 pF	[3]	
C11, C12	multilayer ceramic chip capacitor	10 pF	[2]	
C15, C16	multilayer ceramic chip capacitor	4.7 μF, 50 V		Kemet C1210X475K5RAC-TU or capacitor of same quality.
C17, C18, C23, C24	multilayer ceramic chip capacitor	100 pF	[2]	
C19, C20	multilayer ceramic chip capacitor	10 μF, 50 V		TDK C570X7R1H106KT000N or capacitor of same quality.
C21, C22	electrolytic capacitor	470 μF; 63 V		
C30	multilayer ceramic chip capacitor	10 pF	<u>[4]</u>	
C31	multilayer ceramic chip capacitor	9.1 pF	<u>[4]</u>	
C32	multilayer ceramic chip capacitor	3.9 pF	<u>[4]</u>	
C33, C34, C35	multilayer ceramic chip capacitor	100 pF	<u>[4]</u>	
C36, C37	multilayer ceramic chip capacitor	4.7 μF, 50 V		TDK C4532X7R1E475MT020U or capacitor of same quality.
L1	microstrip	-	<u>[5]</u>	(W × L) 15 mm × 13 mm
L2	microstrip	-	<u>[5]</u>	$(W \times L)$ 5 mm $\times$ 26 mm
L3, L32	microstrip	-	<u>[5]</u>	(W $\times$ L) 2 mm $\times$ 49.5 mm
L4	microstrip	-	<u>[5]</u>	(W × L) 1.7 mm 3.5 mm
L5	microstrip	-	<u>[5]</u>	$(W \times L)$ 2 mm $\times$ 9.5 mm
L30	microstrip	-	<u>[5]</u>	$(W \times L)$ 5 mm $\times$ 13 mm
L31	microstrip	-	<u>[5]</u>	(W × L) 2 mm × 11 mm
L33	microstrip	-	<u>[5]</u>	$(W \times L)$ 2 mm $\times$ 3 mm
R1, R2	wire resistor	10 Ω		

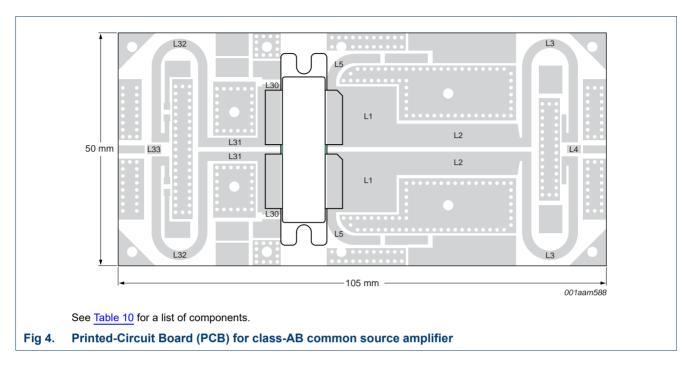
**Power LDMOS transistor** 

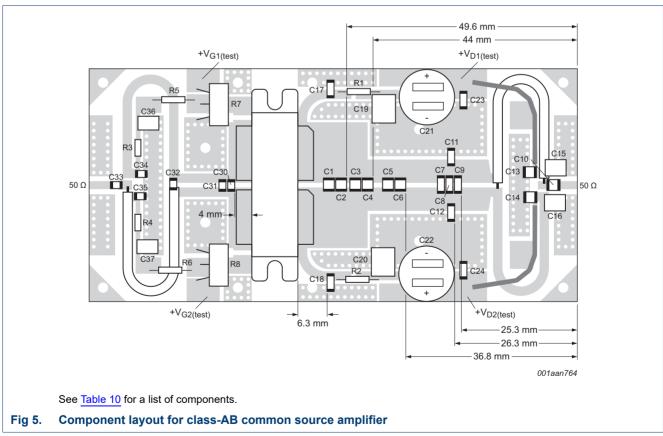
#### Table 10. List of components ... continued

For test circuit, see Figure 3, Figure 4 and Figure 5.

Component	Description	Value	Remarks
R3, R4	SMD resistor	5.6 Ω	0805
R5, R6	wire resistor	100 Ω	
R7, R8	potentiometer	10 kΩ	

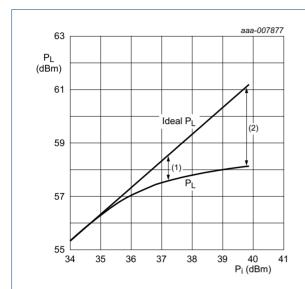
- [1] American technical ceramics type 800R or capacitor of same quality.
- [2] American technical ceramics type 800B or capacitor of same quality.
- [3] American technical ceramics type 180R or capacitor of same quality.
- [4] American technical ceramics type 100A or capacitor of same quality.
- [5] Printed-Circuit Board (PCB): Taconic RF35;  $\epsilon_r$  = 3.5 F/m; height = 0.762 mm; Cu (top/bottom metallization); thickness copper plating = 35  $\mu$ m.





### 7.4 Graphical data

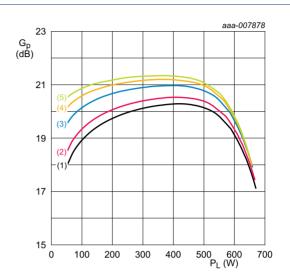
### **7.4.1 Pulsed**



 $V_{DS}$  = 50 V;  $I_{Dq}$  = 1300 mA; f = 860 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 20 %.

- (1)  $P_{L(1dB)} = 57.6 \text{ dBm } (575 \text{ W})$
- (2)  $P_{L(3dB)} = 58.1 \text{ dBm } (649 \text{ W})$

Fig 6. Output power as a function of input power; typical values

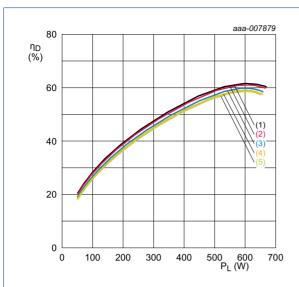


 $V_{DS}$  = 50 V; f = 860 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %.

- (1)  $I_{Dq} = 100 \text{ mA}$
- (2)  $I_{Dq} = 200 \text{ mA}$
- (3)  $I_{Dq} = 600 \text{ mA}$
- (4)  $I_{Dq} = 1000 \text{ mA}$
- (5)  $I_{Dq} = 1300 \text{ mA}$

Fig 7. Power gain as a function of output power; typical values

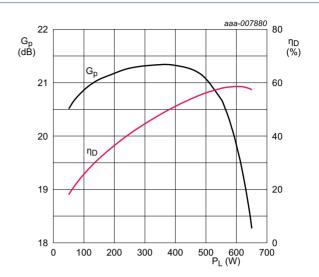
**Power LDMOS transistor** 



 $V_{DS}$  = 50 V; f = 860 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %.

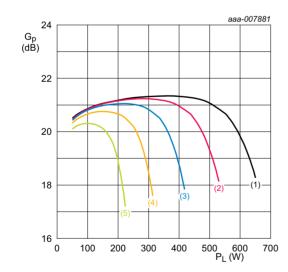
- (1)  $I_{Dq} = 100 \text{ mA}$
- (2)  $I_{Dq} = 200 \text{ mA}$
- (3)  $I_{Dq} = 600 \text{ mA}$
- (4)  $I_{Dq} = 1000 \text{ mA}$
- (5)  $I_{Dq} = 1300 \text{ mA}$





 $V_{DS}$  = 50 V;  $I_{Dq}$  = 1300 mA; f = 860 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 20 %.

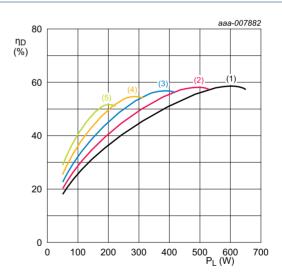
## Fig 9. Power gain and drain efficiency as function of output power; typical values



 $I_{Dq}$  = 1300 mA; f = 860 MHz;  $t_p$  = 100  $\mu s;$   $\delta$  = 20 %.

- (1)  $V_{DS} = 50 \text{ V}$
- (2)  $V_{DS} = 45 \text{ V}$
- (3)  $V_{DS} = 40 \text{ V}$
- (4)  $V_{DS} = 35 \text{ V}$
- (5)  $V_{DS} = 30 \text{ V}$

Fig 10. Power gain as a function of output power; typical values

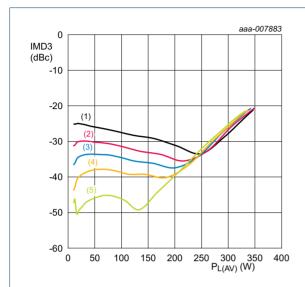


 $I_{Dq}$  = 1300 mA; f = 860 MHz;  $t_p$  = 100  $\mu$ s;  $\delta$  = 20 %.

- (1)  $V_{DS} = 50 \text{ V}$
- (2)  $V_{DS} = 45 \text{ V}$
- (3)  $V_{DS} = 40 \text{ V}$
- (4)  $V_{DS} = 35 V$
- (5)  $V_{DS} = 30 \text{ V}$

Fig 11. Drain efficiency as a function of output power; typical values

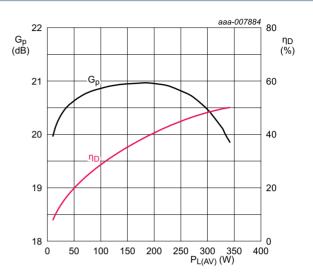
### 7.4.2 2-Tone CW



 $V_{DS} = 50 \text{ V}$ ;  $f_1 = 860.0 \text{ MHz}$ ;  $f_2 = 860.1 \text{ MHz}$ .

- (1)  $I_{Dq} = 600 \text{ mA}$
- (2)  $I_{Dq} = 1000 \text{ mA}$
- (3)  $I_{Dq} = 1300 \text{ mA}$
- (4)  $I_{Dq} = 1600 \text{ mA}$
- (5)  $I_{Dq} = 2000 \text{ mA}$

Fig 12. Third-order intermodulation distortion as a function of average output power; typical values



 $V_{DS}$  = 50 V;  $I_{Dq}$  = 1300 mA;  $f_1$  = 860.0 MHz;  $f_2$  = 860.1 MHz.

Fig 13. Power gain and drain efficiency as function of average output power; typical values

## 8. Package outline

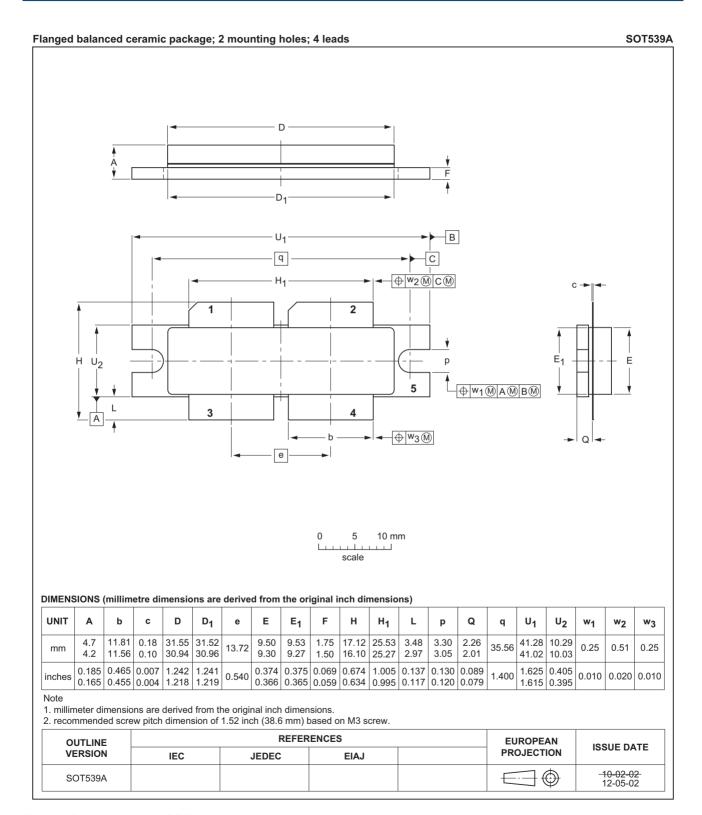


Fig 14. Package outline SOT539A

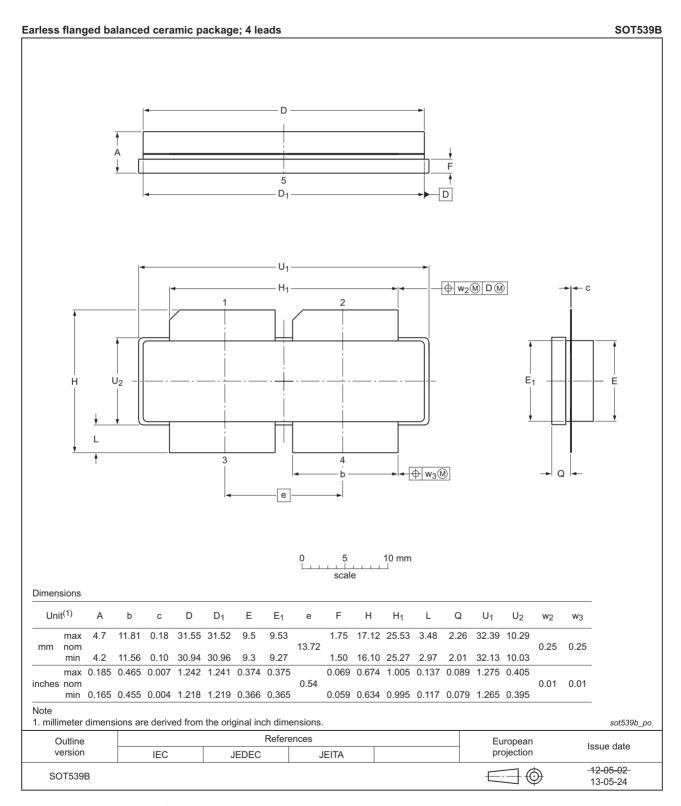


Fig 15. Package outline SOT539B

## 9. Handling information

### CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

## 10. Abbreviations

Table 11. Abbreviations

Acronym	Description
CCDF	Complementary Cumulative Distribution Function
CW	Continuous Wave
LDMOS	Laterally Diffused Metal-Oxide Semiconductor
SMD	Surface Mounted Device
VSWR	Voltage Standing-Wave Ratio

## 11. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes	
BLF10H6600P_BLF10H6600PS#3	20150901	Product data sheet	-	BLF10H6600P_BLF1 0H6600PS v.2	
Modifications:	<ul> <li>The format of this document has been redesigned to comply with the new identity guidelines of Ampleon.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> </ul>				
BLF10H6600P BLF10H6600PS v.2	20130620	Product data sheet	-	BLF0510H6600P v.1	
BLF0510H6600P v.1	20121009	Objective data sheet	-	-	

### 12. Legal information

### 12.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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